

**2SC4204**

High- h_{FE} , AF Amplifier Applications

Applications

- AF amplifier, various drivers.

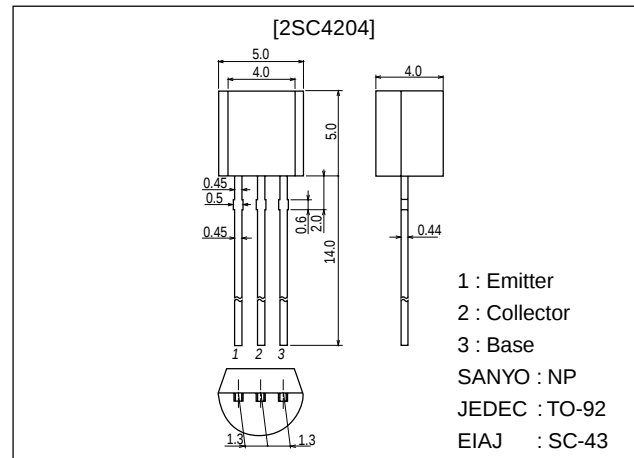
Features

- Adoption of MBIT process.
- High DC current gain ($h_{FE}=800$ to 3200).
- Large current capacity ($I_C=0.7A$).
- Low collector-to-emitter saturation voltage ($V_{CE(sat)}\leq 0.5V$).
- High V_{EBO} ($V_{EBO}\geq 15V$).

Package Dimensions

unit:mm

2003B



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		30	V
Collector-to-Emitter Voltage	V_{CEO}		25	V
Emitter-to-Base Voltage	V_{EBO}		15	V
Collector Current	I_C		0.7	A
Collector Current (Pulse)	I_{CP}		1.5	A
Collector Dissipation	P_C		0.6	W
Junction Temperature	T_J		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=10V, I_C=0$			0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=50mA$	800	1500	3200	
	h_{FE2}	$V_{CE}=5V, I_C=500mA$	600			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=50mA$		270		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		9		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=10mA$		0.15	0.50	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=10mA$		0.9	1.2	V

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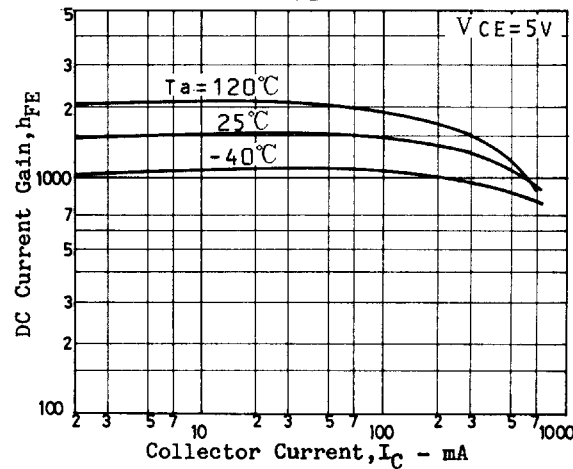
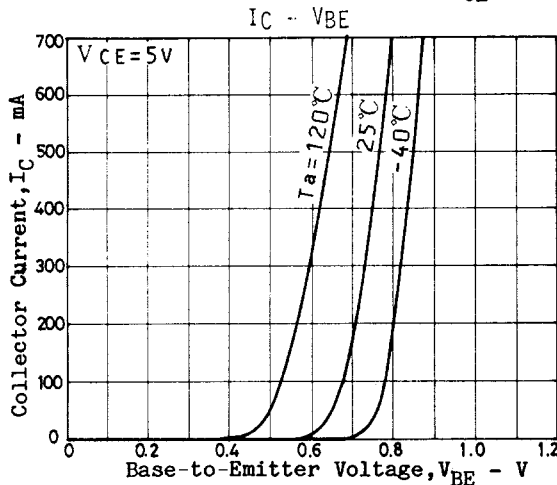
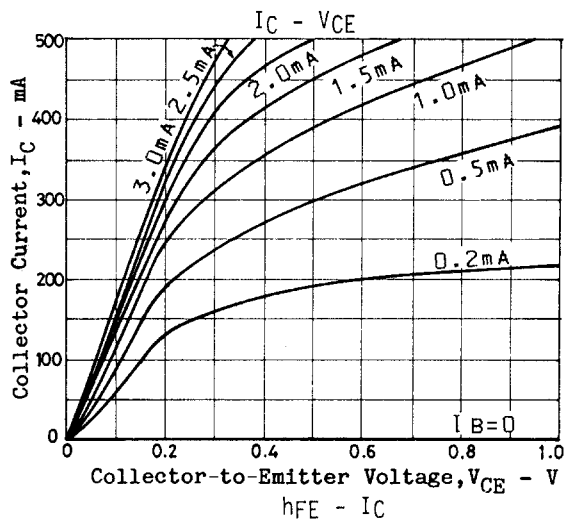
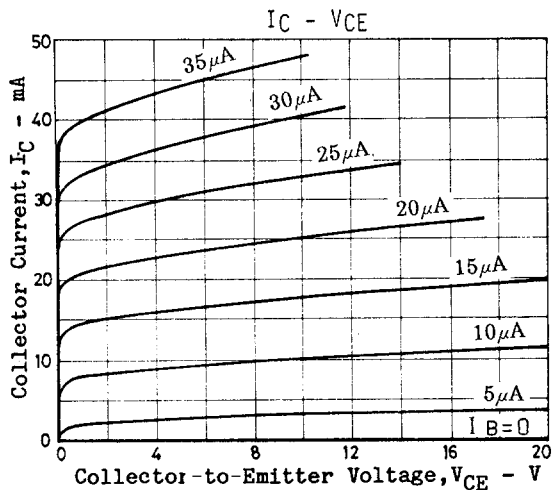
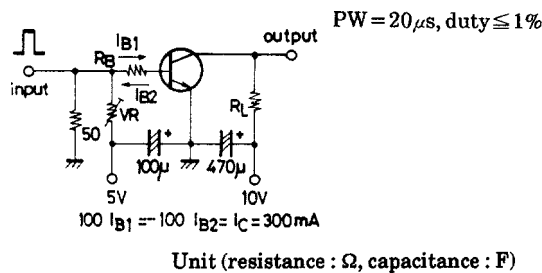
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D1598HA (KT)/4231, 4217TA, TS No.2531-1/4

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V
Turn-ON Time	t_{on}	See specified test circuit.		0.1		μs
Storage Time	t_{stg}	See specified test circuit.		0.6		μs
Fall Time	t_f	See specified test circuit.		0.06		μs

Switching Time Test Circuit



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